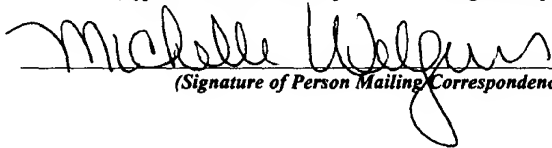


CERTIFICATE OF MAILING BY FIRST CLASS MAIL (37 CFR 1.8)			Docket No.
Applicant(s): Takayoshi Sawayama			OKI.201
Serial No. 09/754,277	Filing Date 01/05/2001	Examiner L. Alejandro	Group Art Unit 1731
Invention: PLASMA ETCHING APPARATUS			
<div style="text-align: center;">COPY OF PAPERS ORIGINALLY FILED</div> <p>I hereby certify that this <u>Amendment</u> <small>(Identify type of correspondence)</small></p> <p>is being deposited with the United States Postal Service as first class mail in an envelope addressed to: The Assistant Commissioner for Patents, Washington, D.C. 20231 on <u>July 15, 2002</u> <small>(Date)</small></p> <div style="text-align: center;"><u>Michelle Welgoss</u> <small>(Typed or Printed Name of Person Mailing Correspondence)</small>  <small>(Signature of Person Mailing Correspondence)</small></div> <p style="text-align: center;">Note: Each paper must have its own certificate of mailing.</p> <div style="text-align: right;">MAILED JUL 23 2002 GROUP 1700</div>			



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Takayoshi Sawayama.

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Group Art Unit: 1731

Serial No.: 09/754,277

Examiner: L. Alejandro

Filed: January 5, 2001

For: PLASMA ETCHING APPARATUS

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JUL 23 2002
GROUP 1700#5A
8/9/02
mwHonorable Commissioner of Patents
Washington, D.C. 20231

Date: July 15, 2002

Amendment

Sir:

In response to the Office Action mailed February 13, 2002, the following amendments and remarks are respectfully submitted in connection with the above captioned application.

Submission of Certified Copy of Priority Document

A certified copy of the priority document, Japanese patent application number 2000-225686 is submitted herewith to ensure compliance with 35 USC § 119(b). Acknowledgement of the receipt thereof is respectfully requested.

In the Specification

(1.) At page 2, line 4, please replace the paragraph that begins "When the gas-introducing plate 4..." with the following paragraph:

When the gas-introducing plate 4 lying within the processing chamber of the etching apparatus is used up, the gas-introducing plate 4 becomes thin as shown in

A1
Sub
B.1